

What is claimed is:

1. A method of manufacturing a semiconductor device, comprising:

5 forming terminal portions convexly protruding on a surface of first conductive foil by etching the first conductive foil except portions to become terminals;

superimposing a resin sheet on the first conductive foil such that the terminal portions are embedded in the resin sheet;

10 constructing a laminated sheet by superimposing second conductive foil on the resin sheet;

forming a conductive pattern by etching the second conductive foil;

electrically connecting the conductive pattern and the terminal portions;

15 electrically isolating the terminal portions from each other;

firmly fixing a semiconductor element to the laminated sheet and electrically connecting the semiconductor element and the conductive pattern; and

20 forming sealing resin on a surface of the laminated sheet such that the semiconductor element is covered by the sealing resin.

25 2. The method according to claim 1, wherein the terminal portions are electrically isolated from each other by etching the first conductive foil from a back thereof.

3. The method according to claim 1, wherein the resin sheet is made of soluble resin, and side surfaces of the terminal portions are exposed by removing the resin sheet.

4. The method according to claim 1, wherein the semiconductor element is connected face-up, and an electrode of the semiconductor element and the conductive pattern are connected through a fine metallic wire.

5 5. The method according to claim 1, wherein the semiconductor element is mounted face-down, and an electrode of the semiconductor element and the conductive pattern are connected through a bump electrode.